



The 23rd Opto-Electronics and Communications Conference

OECC 2018

Conference Program & Abstracts

July 2 – 6, 2018

ICC Jeju, Korea

- **Organized by**

Optical Society of Korea (OSK)

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OECC 2018 Program

July 02 (Mon.)								
	Samda Hall A (Room A)	Samda Hall B (Room B)	301 (Room C)	302 (Room D)	Halla Hall A (Room E)	303 (Room F)	Lobby(3F)	
14:00-17:00	180'		Workshop I Direct Detection vs. Coherent Detection for Short- and Intermediate-Haul Applications	Workshop II Silicon Photonics			Registration (12:00-18:00)	
17:00-18:00	60'	-						
18:00-20:00	Get-Together Party (Ocean View, 5F)							

July 03 (Tue.)								
08:45-09:00	15'	Opening ceremony						Exhibition
09:00-09:45	45'	Plenary Talk I - Roel Baets (Halla Hall, 3F)						
09:45-10:30	45'	Plenary Talk II - Masatoshi Suzuki (Halla Hall, 3F)						
10:30-11:00	30'	Coffee Break						
11:00-11:45	45'	Plenary Talk III - Sanghoon Lee (Halla Hall, 3F)						
11:45-12:30	45'	Plenary Talk IV - Chongjin Xie (Halla Hall, 3F)						
12:30-14:00	90'	Lunch						
14:00-15:30	90'	3A1 Mode Division Multiplexing	3B1 Direct-Detection Systems	3C1 Optical Fiber Applications	3D1 Silicon Photonics	3E1 Passive Devices	3F1 [Symposium I] 10Giga Internet and Broadband Access	
15:30-16:00	30'	Coffee Break						
16:00-17:30	90'	3A2 Photonic Signal Processing 1	3B2 Capacity-Approaching Techniques	3C2 Specialty Fibers	3D2 Optical Transmitter 1	3E2 Integrated Photonics 1	3F2 [Symposium I] 10Giga Internet and Broadband Access	

July 04 (Wed.)								
08:30-10:00	90'	4A1 Photonic Signal Processing 2	4B1 High Spectral Efficiency	4C1 Fiber Fabrication and Applications	4D1 Optical Transmitter 2	4E1 Integrated Photonics 2	-	Exhibition
10:00-10:30	30'	Coffee Break						
10:30-12:00	90'	4A2 Short Reach Networks	4B2 Light Propagation in Fiber	4C2 Fiber Amplifiers	4D2 Photonic Crystal	4E2 Silicon Photonics 1	4F2 [Industrial I] High Power Fiber Lasers for Industrial Applications	
12:00-13:00	60'	Lunch						
13:00-14:00	60'	Poster Session I (Lobby, 3F)						
14:00-15:30	90'	4A3 Optical Access for 5G 1	4B3 Nonlinear Transmission	4C3 Fiber Amplifiers and Light Sources	4D3 Optical Transmitter 3	4E3 Silicon Photonics 2	4F3 [Symposium II] Recent Advances in Photonic Packaging Technologies	
15:30-16:00	30'	Coffee Break						
16:00-17:30	90'	4A4 Optical Wireless Access	4B4 SSB DD Systems	4C4 Fiber Lasers	4D4 Optical Receivers	4E4 Silicon Photonics 3	4F4 [Symposium II] Recent Advances in Photonic Packaging Technologies	
17:30-18:30		-						
18:30-20:30		Banquet						

July 05 (Thu.)								
08:30-10:00	90'	5A1 Indoor Network	5B1 Polarization Issues & Monitoring	5C1 Optical Fiber Sensors	5D1 Secure & Free-Space Communications	5E1 Sensing Devices	-	Exhibition
10:00-10:30	30'	Coffee Break						
10:30-12:00	90'	5A2 High Speed PON	5B2 Space Division Multiplexing	5C2 Nonlinear Interaction of Light	5D2 Photonic Integrated Circuits	5E2 Fiber Devices	5F2 [Industrial II] 5G and Photonics	
12:00-13:00	60'	Lunch						
13:00-14:00	60'	Poster Session II (Lobby, 3F)						
14:00-15:30	90'	5A3 Signal Processing for Access Network	5B3 High Capacity Transmission	5C3 Optical Fibers for SDM	5D3 Quantum Communication Devices	5E3 Photonic Devices 1	5F3 [Symposium III] State of the Art in Distributed Fiber Sensors	
15:30-16:00	30'	Coffee Break						
16:00-17:30	90'	5A4 Optical Access for 5G 2	5B4 Transceiver Technologies	5C4 Specialty Fibers for High Power Lasers	5D4 Advanced Optical Devices 1	5E4 Photonic Devices 2	5F4 [Symposium III] State of the Art in Distributed Fiber Sensors	
17:30-18:00		-						
18:00-19:00	60'	PDP Session						

July 06 (Fri.)								
08:30-10:00	90'	6A1 Novel Algorithm for Optical Network	6B1 Performance Monitoring	6C1 Distributed Fiber Sensing	6D1 Advanced Optical Devices 2	6E1 Photonics Devices 3	-	-
10:00-10:30	30'	Coffee Break						
10:30-12:00	90'	6A2 Visible Light Communication	6B2 Technologies for Datacenter Applications	6C2 Access Network Technologies	6D2 Digital Signal Processing	-	-	

Tuesday, July 3

Room D (302)	Room E (Halla Hall A)	Room F (303)
<p>[3D2] 16:00-17:30 Optical Transmitter 1 <i>Session Chair : Nicola Calabretta (TU/e)</i></p>	<p>[3E2] 16:00-17:30 Integrated Photonics 1 <i>Session Chair : Benjamin J. Eggleton (The Univ. of Sydney)</i></p>	<p>[3F2] 16:00-17:30 [Symposium 1] 10Giga Internet and Broadband Access <i>Session Chair : Xiang Liu (Huawei) T.Nirmalathas (The Univ. of Melbourne)</i></p>
<p>3D2-1 16:00-16:30 (30') Invited Modeling Depletion-Type Si Ring Modulators <i>Woo-Young Choi¹, Minkyu Kim¹, Myungjin Shin¹, Byung-Min Yu¹, Christian Mai², Stefan Lischke², and Lars Zimmermann².</i> ¹Yonsei Univ., Korea, ²IHP, Germany For achieving monolithic integration of Si electronics and photonics, accurate and convenient-to-use models for Si photonic devices are very important. We present such a model for depletion-type Si ring modulators.</p>	<p>3E2-1 16:00-16:30 (30') Invited Silicon Nitride (TriPleX™) based Photonic Integrated Circuits for a Broad Range of Application Modules <i>Arne Leinse Lionix Int^l, Netherlands</i> An overview of recent developments of the SiN based TriPleX™ Photonic-Integrated-Circuit technology is given. The unique features of the technology are explained and application examples in a variety of wavelength ranges are shown.</p>	<p>3F2-1 16:00-16:30 (30') Invited State of Broadband Access and High Speed PON <i>Hyung Jin Park KT, Korea</i></p>
<p>3D2-2 16:30-17:00 (30') Invited Ultra-Low-Power Microring Modulators for PAM and WDM Links <i>Wej Shi and Yelong Xu Université Laval, Canada</i> We review our recent results on low-power microring modulators for pulse-amplitude modulation and high-quality frequency comb generation. This single-laser WDM solution is promising for next-generation optical interconnects.</p>	<p>3E2-2 16:30-17:00 (30') Invited Integrated Polarization Diversity Devices <i>Kyong Hon Kim¹, Yudeuk Kim¹, Yoohan Kim¹, Dong Wook Kim¹, and Moon Hyeok Lee²</i> ¹Inha Univ., Korea, ²Heinrich Hertz Inst., Germany Integrated polarization diversity devices, such as polarization beam splitter, polarization rotator, and polarizer, are very important in silicon-based photonic integrated circuits. The integrated polarization diversity devices are introduced, and experimentally demonstrated results are reported.</p>	<p>3F2-2 16:30-17:00 (30') Invited Broadband Access in Japan and Flexible Optical Access <i>Sangyeup Kim NTT Corp., Japan</i></p>
<p>3D2-3 17:00-17:15 (15') <u>A Wavelength Stabilization Integrated Circuit for 25-Gb/s Si Micro-Ring Modulator</u> <i>Min-Hyeong Kim¹, Lars Zimmermann², and Woo-Young Choi¹</i> ¹Yonsei Univ., Korea, ²IHP, Germany We demonstrate wavelength stabilization of Si microring modulator (MRM) with an integrated circuit custom-designed in 0.25-μm BiCMOS technology. Our circuit controls the MRM temperature so that it can have the maximum optical modulation amplitude with 25-Gb/s modulation.</p>	<p>3E2-3 17:00-17:15 (15') Two- and Three-Dimensional Polymer Directional Coupler for High-Density Optical Interconnects at 1550 nm <i>Xiao Xu, Lin Ma, and Zuyuan He Shanghai Jiaotong Univ., China</i> We demonstrate two- and three-dimensional single-mode polymer directional coupler directly inscribed using a micro-dispenser. We successfully fabricated two-core couplers with splitting ratios of 0.95 and 0.52 and three-dimensional couplers operating at 1550 nm.</p>	<p>3F2-3 17:00-17:30 (30') Invited Deployment of 10G Internet and Broadband Access: Korean Story <i>Sung-uk Rha NIA, Korea</i></p>
<p>3D2-4 17:15-17:30 (15') An Actively Mode-Locked Laser based on a 5th Order Micro-Ring Resonator <i>Qihong Wu¹, Yuhua Li², Shaohao Wang³, Qian Li¹, and Sai Tak Chu²</i> ¹Peking Univ., China, ²City Univ. of Hong Kong, China, ³Fuzhou Univ., China We present a mode locked laser configuration with an integrated 5th order micro-ring resonator, where highly stable pulse trains with single and multiple pulses per period have been achieved.</p>	<p>3E2-4 17:15-17:30 (15') Analytical Investigation of Generic Form Expressing Adaptive Dispersion of Optical Fractional Fourier Transform Circuit <i>Tomohiro Naganuma and Hiroyuki Uenohara Tokyo Inst. of Tech., Japan</i> We clarified the regularity of the dispersion performance of an optical fractional Fourier transform circuit, realizing variable dispersion compensation in an optical OFDM system. The generic form of dispersion performance is presented.</p>	

A Wavelength Stabilization Integrated Circuit for 25-Gb/s Si Micro-Ring Modulator

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Abstract

We demonstrate wavelength stabilization of Si micro-ring modulator (MRM) with an integrated circuit custom-designed in 0.25- μm BiCMOS technology. Our circuit controls the MRM temperature so that it can have the maximum optical modulation amplitude (OMA). It consists of trans-impedance amplifier, power detector, track-and-hold circuit, comparator, digital-to-analog converter, and synthesized digital controller. 25-Gb/s MRM modulation is achieved with the wavelength stabilization IC.

I. INTRODUCTION

As the demand for commercial data centers and mobile devices are rapidly increasing, the application of high-bandwidth photonic solutions is extending from medium-and-long distance communications to short reach interconnects. There is a great interest in Si micro-ring modulators (MRMs) for short-reach interconnect applications, as they provide high modulation speed and small size [1]. However, the Si MRM has a serious drawback in that its characteristics are very easily influenced by the temperature. Fig. 1 shows the Si MRM used in the present investigation, which was fabricated with IME foundry service. It also shows its measured transmission characteristics at various temperatures. With about 80-pm/ $^{\circ}\text{C}$ change for its resonance wavelength is changed to about, a wavelength stabilization (λ -stabilization) circuit is indispensable for its practical use [2]. There are several previous reports on realization of the λ -stabilization circuit [3,4], but very few on its integrated circuit (IC) implementation [5,6], which is absolutely required for any practical application of Si MRMs. In this paper, we demonstrate a novel Si MRM wavelength stabilization circuit implemented in IHP's 0.25- μm BiCMOS technology, which directly measures Si MRM OMA and provides control voltages to the on-chip heater next to Si MRM for achieving optimal MRM operation.

II. STABILIZATION CIRCUIT

The dotted box in fig. 2 shows the block diagram of the λ -stabilization circuit. TIA, power detector, T/H circuit, and comparator are used for monitoring the OMA and DAC and digital circuit (Counter) are used for controlling the heater voltage (V_{HEAT}), all of which are integrated monolithically.

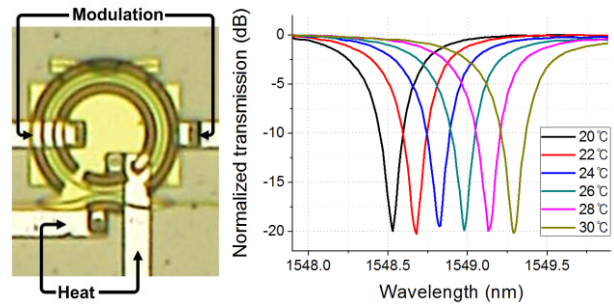


Figure 1. Microphotograph of Si MRM and its normalized transmission spectra at six different external temperatures

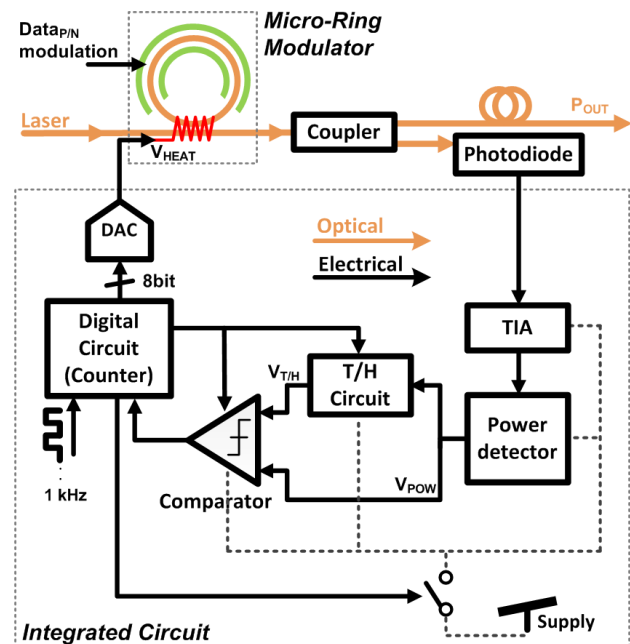


Figure 2. Block diagram of proposed wavelength stabilization circuit with optical setup

In our λ -stabilization circuit, the built-in controller scans V_{HEAT} while measuring OMA at each value of V_{HEAT} . The V_{HEAT} that produces that optimal OMA is determined and, then, the optimal V_{HEAT} can be automatically maintained continuously [7]. We also implement two-step approaches of 'coarse-scan and fine-control' steps for achieving a fast initial acquisition. In the first step, the full range of V_{HEAT} by the DAC is coarsely scanned with increasing N-bit step by step. Depending on the situation, a size of the N can be digitally adjustable. In the second step, detailed and continuous OMA optimization is performed through 1-bit DAC control. To save the power consumption, a low-

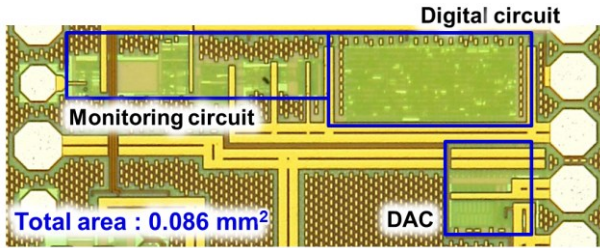


Figure 3. Microphotograph of the fabricated λ -stabilization circuit

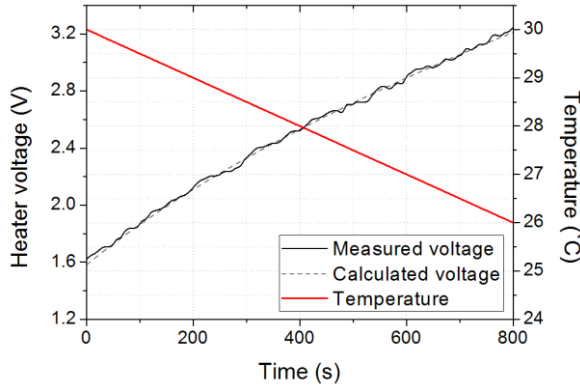


Figure 4. External temperature variations to MRM and measured heater voltages controlled by the λ -stabilization circuit

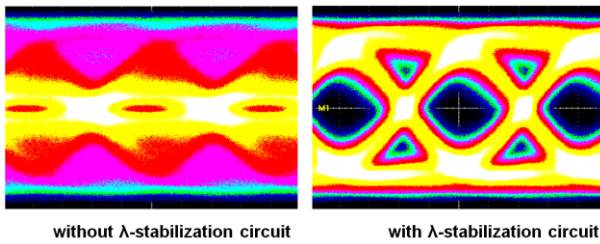


Figure 5. Measured 25-Gb/s PRBS7 eye diagrams accumulated for 13.3 min (a) without and (b) with the λ -stabilization circuit while external temperature variations are supplied as shown in Figure 4.

power strategy is employed in which the monitoring circuits are turned on periodically only for a short amount of time.

III. MEASUREMENT RESULTS

Fig. 2 shows the measurement setup. A depletion-type Si MRM is modulated by 25-Gb/s PRBS-7 data and its output is coupled into a commercial photodiode for monitoring OMA. 1-kHz pulse signal is externally introduced as the clock signal for the digital circuit. Fig. 3 shows the photograph of our λ -stabilization IC. Its area is approximately 0.086-mm^2 . The total power consumption is 6.26-mW.

In order to demonstrate the operation of our λ -stabilization IC, the temperature of MRM is intentionally ramped from 30°C to 26°C with the ramping speed of $5\text{-m}^\circ\text{C}/\text{sec}$. Fig. 4 shows the measured V_{HEAT} provided by our stabilization circuit during this ramp. The measured 25Gbps eye during this temperature is shown in Fig. 5(a). The degradation in eye quality is due to the shift of MRM resonance wavelength. With our λ -stabilization IC on, however, the eye can be maintained open as shown in Fig. 5(b).

IV. CONCLUSIONS

In this paper, we demonstrated a new fully-integrated wavelength stabilization circuit based on OMA monitoring for Si MRM. A prototype chip realized in IHP's $0.25\text{-}\mu\text{m}$ BiCMOS technology is successfully demonstrated. With the IHP's Si Photonic BiCMOS technology, which integrates $0.25\text{-}\mu\text{m}$ BiCMOS electronics with high performance Si photonic devices, our λ -stabilization IC can be monolithically integrated with Si MRM along with a monitor Ge photodetector, resulting in a complete integrated solution for Si MRM transmitters.

ACKNOWLEDGMENT

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